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DBs: USPAT, EPO, JPO, DERWENT, IBM, TDB Plurals

Default operator: OR Highlight all hit terms initially

signal adj. wiring and shield and memory

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Rank	Category	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	□	US 6693334 B2	20040217	18	Semiconductor integrated circuit device	257/409	257/503, 257/774
2	□	US 6681375 B2	20040120	13	Check system for wiring structure of printed circuit board	716/4	716/15, 716/5
3	□	US 6657901 B2	20031202	162	Semiconductor device formed in a rectangle region on a semiconductor	365/189.02	257/E23.02; 365/51,
4	□	US 6650574 B2	20031118	18	Semiconductor device preventing signal delay among wirings	365/194	327/108; 327/261,
5	□	US 6611107 B2	20030826	24	Image display apparatus	315/169.1	257/59; 257/72,
6	□	US 6583456 B2	20030624	53	Image sensor with light receiving elements of differing areas and image reader both	257/292	257/291; 257/443,
7	□	US 6530066 B1	20030304	22	Method of computing wiring capacitance, method of computing signal propagation	716/5	438/599; 703/15,
8	□	US 6515913 B2	20030204	160	Semiconductor memory device and defect remedying method thereof	365/189.02	257/E23.02; 365/230.02;
9	□	US 6506664 B1	20030114	23	Method of transferring ultra-thin substrates and application of the method to the	438/455	257/E21.705; 257/E23.172;
10	□	US 6504237 B2	20030107	22	Semiconductor with multilayer metal structure using copper that offer high	257/666	257/296; 257/E23.144,
11	□	US 6483493 B2	20021119	41	Electro-optical apparatus and electronic device	345/87	345/100; 345/98

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